



AOS Semiconductor Product Reliability Report

AON5802B/L, rev B

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

www.aosmd.com

This AOS product reliability report summarizes the qualification result for AON5802B/L. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AON5802B/L passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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I. Product Description:

The AON5802B/L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V while retaining a 12V $V_{GS(MAX)}$ rating. This device is suitable for use as a unidirectional or bi-directional load switch, facilitated by its common-drain configuration.

- RoHS Compliant
- AON5802BL is Halogen Free

Detailed information refers to datasheet.

II. Die / Package Information:

	AON5802B/L
Process	Standard sub-micron
	Low voltage N channel, dual die
Package Type	DFN 2x5
Lead Frame	Copper
Die Attach	Silver epoxy
Bonding Wire	Cu &Au wire
Mold Material	Epoxy resin with silica filler
MSL (moisture sensitive level)	Level 1 based on J-STD-020

Note * based on information provided by assembler and mold compound supplier

III. Result of Reliability Stress for AON5802B/L

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures	Standard
MSL Precondition	168hr 85°C /85%RH +3 cycle reflow@260°C	-	11 lots	1815pcs	0	JESD22-A113
HTGB	Temp = 150 °c, Vgs=100% of Vgsmax	168hrs 500 hrs 1000 hrs	2 lots 1 lot (Note A*)	231pcs 77pcs / lot	0	JESD22-A108
HTRB	Temp = 150 °c, Vds=80% of Vdsmax	168hrs 500 hrs 1000 hrs	2 lots 1 lot (Note A*)	231pcs 77pcs / lot	0	JESD22-A108
HAST	130 +/- 2°C, 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	11 lots (Note A*)	605pcs 55pcs / lot	0	JESD22-A110
Pressure Pot	121°C, 29.7psi, RH=100%	96 hrs	11 lots (Note A*)	605pcs 55pcs / lot	0	JESD22-A102
Temperature Cycle	-65°C to 150°C, air to air	250 / 500 cycles	11 lots (Note A*)	605pcs 55pcs / lot	0	JESD22-A104

Note A: The reliability data presents total of available generic data up to the published date.

IV. Reliability Evaluation

FIT rate (per billion): 28

MTTF = 4144 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AON5802B/L). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)]$$

$$= 1.83 \times 10^9 / [2 \times (2 \times 2 \times 77 \times 168 + 2 \times 77 \times 500) \times 258] = 28$$

$$\text{MTTF} = 10^9 / \text{FIT} = 3.63 \times 10^7 \text{ hrs} = 4144 \text{ years}$$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = **Exp** [Ea / k (1/Tj u - 1/Tj s)]

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

K = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K